

# 2SK3471

## Switching Regulator and DC-DC Converter Applications

- Low drain-source ON resistance:  $R_{DS(ON)} = 10 \Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 0.4 \text{ S}$  (typ.)
- Low leakage current:  $I_{DSS} = 100 \mu\text{A}$  (max) ( $V_{DS} = 500 \text{ V}$ )
- Enhancement-model:  $V_{th} = 2.0$  to  $4.0 \text{ V}$  ( $V_{DS} = 10 \text{ V}$ ,  $I_D = 1 \text{ mA}$ )

### Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	500	V
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		$V_{DGR}$	500	V
Gate-source voltage		$V_{GSS}$	$\pm 30$	V
Drain current	DC (Note 1)	$I_D$	0.5	A
	Pulse (Note 1)	$I_{DP}$	1.5	
Drain power dissipation		$P_D$	0.5	W
Drain power dissipation (Note 2)		$P_D$	1.5	W
Single pulse avalanche energy (Note 3)		$E_{AS}$	14.3	mJ
Avalanche current		$I_{AR}$	0.5	A
Repetitive avalanche energy (Note 4)		$E_{AR}$	0.05	mJ
Channel temperature		$T_{ch}$	150	$^\circ\text{C}$
Storage temperature range		$T_{stg}$	-55 to 150	$^\circ\text{C}$

### Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	250	$^\circ\text{C/W}$

Note 1: Please use devices on condition that the channel temperature is below  $150^\circ\text{C}$ .

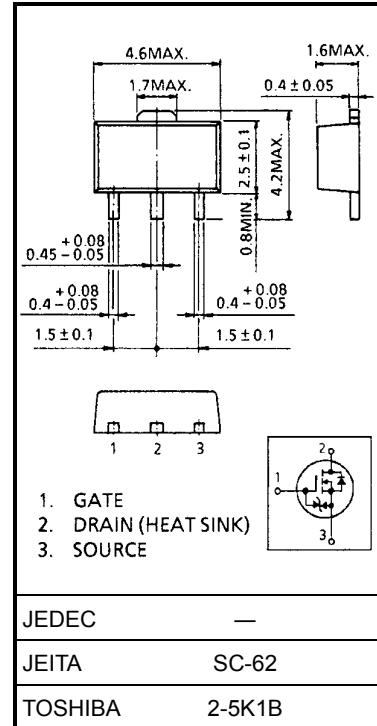
Note 2: Mounted on ceramic substrate ( $25.4 \text{ mm} \times 25.4 \text{ mm} \times 0.8 \text{ mm}$ )

Note 3:  $V_{DD} = 90 \text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 100 \text{ mH}$ ,  $R_G = 25 \Omega$ ,  $I_{AR} = 0.5 \text{ A}$

Note 4: Repetitive rating: Pulse width limited by maximum channel temperature

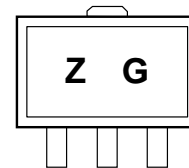
This transistor is an electrostatic sensitive device. Please handle with caution.

Unit: mm



Weight: 0.05 g (typ.)

### Marking



(The two digits represent the part number.)

## Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)GSS}$	$I_G = \pm 10 \mu\text{A}, V_{DS} = 0 \text{ V}$	$\pm 30$	—	—	V
Drain cut-OFF current		$I_{DSS}$	$V_{DS} = 500 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	100	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	500	—	—	V
Gate threshold voltage		$V_{th}$	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	2.0	—	4.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10 \text{ V}, I_D = 0.25 \text{ A}$	—	10	18	$\Omega$
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10 \text{ V}, I_D = 0.25 \text{ A}$	0.2	0.4	—	S
Input capacitance		$C_{iss}$	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	75	—	pF
Reverse transfer capacitance		$C_{rss}$		—	7	—	
Output capacitance		$C_{oss}$		—	24	—	
Switching time	Rise time	$t_r$		—	11	—	ns
	Turn-ON time	$t_{on}$		—	18	—	
	Fall time	$t_f$		—	54	—	
	Turn-OFF time	$t_{off}$		Duty $\leq 1\%$ , $t_w = 10 \mu\text{s}$	—	95	
Total gate charge (gate-source plus gate-drain)		$Q_g$	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 0.5 \text{ A}$	—	3.8	—	nC
Gate-source charge		$Q_{gs}$		—	1.9	—	
Gate-drain ("miller") charge		$Q_{gd}$		—	1.9	—	

## Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	$I_{DR}$	—	—	—	0.5	A
Pulse drain reverse current (Note 1)	$I_{DRP}$	—	—	—	1.5	A
Forward voltage (diode)	$V_{DSF}$	$I_{DR} = 0.5 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	-1.5	V
Reverse recovery time	$t_{rr}$	$I_{DR} = 0.5 \text{ A}, V_{GS} = 0 \text{ V},$	—	190	—	ns
Reverse recovery charge	$Q_{rr}$	$dI_{DR}/dt = 100 \text{ A}/\mu\text{s}$	—	380	—	nC

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